

BYW29-200

SWITCHMODE™ Power Rectifiers

This state-of-the-art device is designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- 175°C Operating Junction Temperature
- Popular TO-220 Package
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Pb-Free Package is Available*

Mechanical Characteristics

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings: Machine Model, C (> 400 V)
Human Body Model, 3B (> 8000 V)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Forward Current Total Device, (Rated V_R), $T_C = 150^\circ\text{C}$	$I_{F(AV)}$	8.0	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz), $T_C = 150^\circ\text{C}$	I_{FM}	16	A
Nonrepetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half-wave, Single Phase, 60 Hz)	I_{FSM}	100	A
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	-65 to +175	°C

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	°C/W
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Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

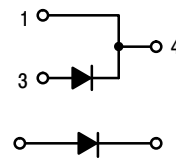
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



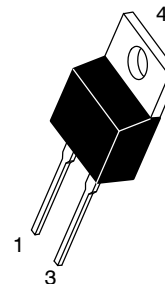
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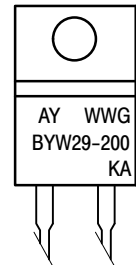
**ULTRAFAST
RECTIFIERS
8.0 AMPERES
200 VOLTS**



MARKING DIAGRAM



**CASE 221B
TO-220B
PLASTIC**



A = Assembly Location
Y = Year
WW = Work Week
BYW80-200 = Device Code
G = Pb-Free Package
KA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
BYW29-200	TO-220	50 Units/Rail
BYW29-200G	TO-220 (Pb-Free)	50 Units/Rail

ELECTRICAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($i_F = 5.0 \text{ A}$, $T_C = 100^\circ\text{C}$) ($i_F = 20 \text{ A}$, $T_C = 25^\circ\text{C}$)	v_F	0.85 1.3	V
Maximum Instantaneous Reverse Current (Note 1) (Rated Dc Voltage, $T_J = 100^\circ\text{C}$) (Rated Dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	600 5.0	μA
Maximum Reverse Recovery Time ($I_F = 1.0 \text{ A}$, $di/dt = 50 \text{ A}/\mu\text{s}$) ($I_F = 0.5 \text{ A}$, $i_R = 1.0 \text{ A}$, $I_{REC} = 0.25 \text{ A}$)	t_{rr}	35 25	ns

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

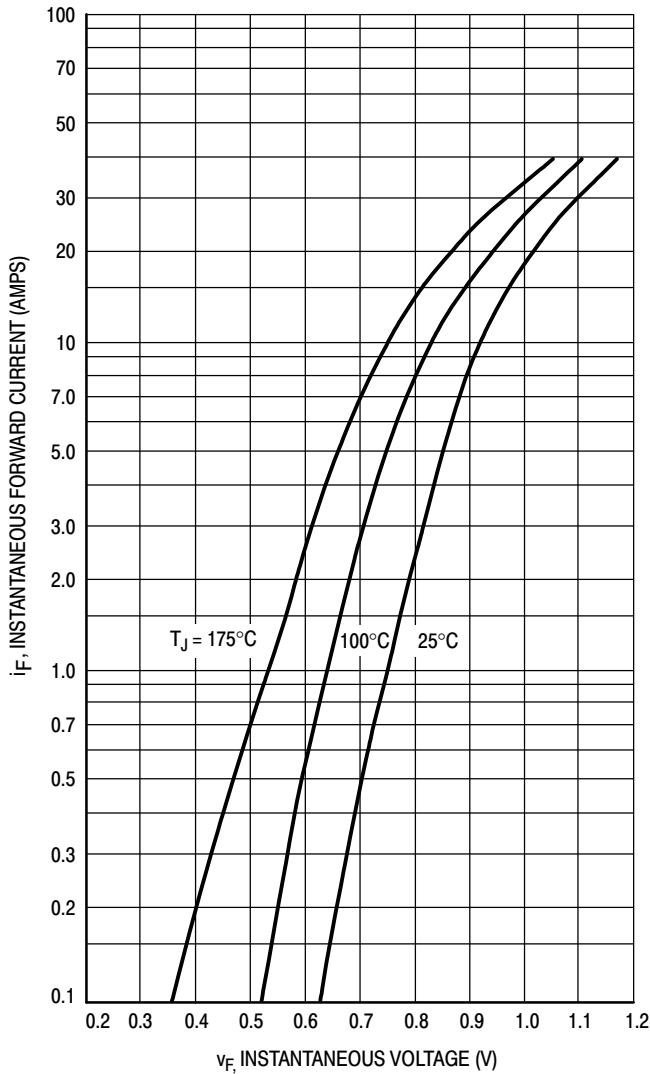


Figure 1. Typical Forward Voltage

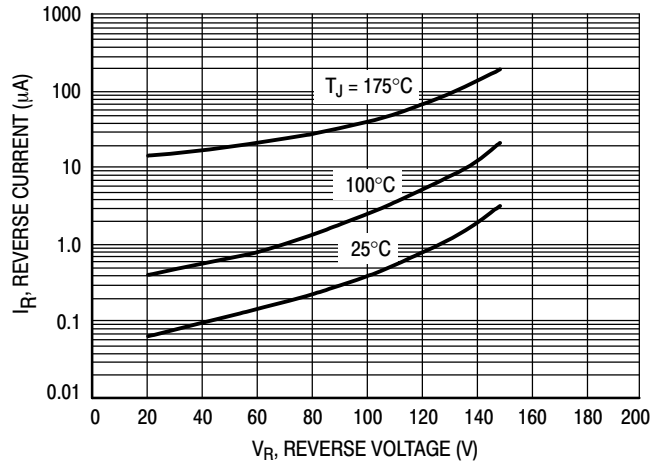


Figure 2. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R .

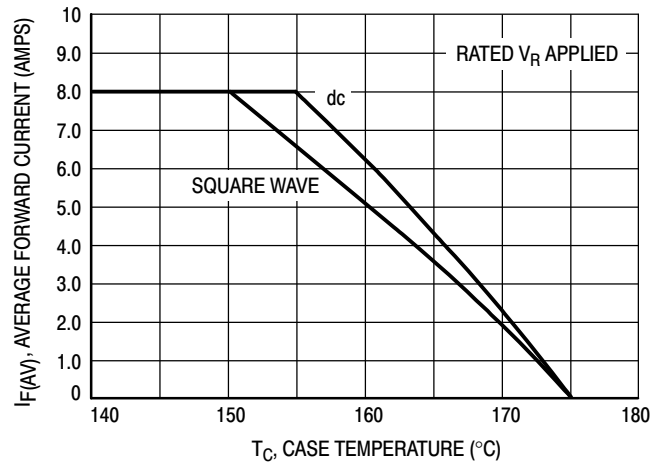


Figure 3. Current Derating, Case

BYW29-200

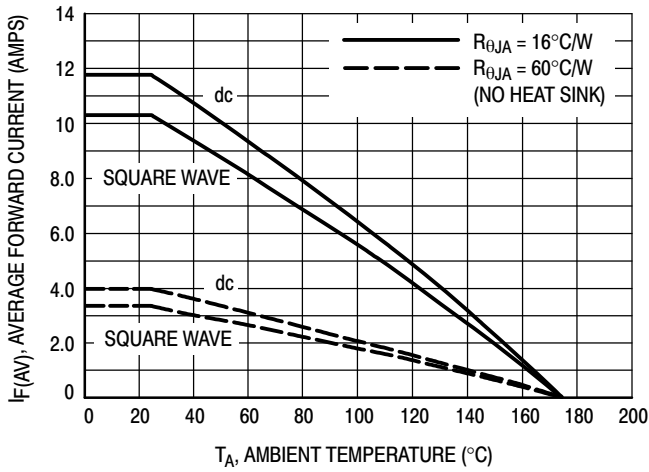


Figure 4. Current Derating, Ambient

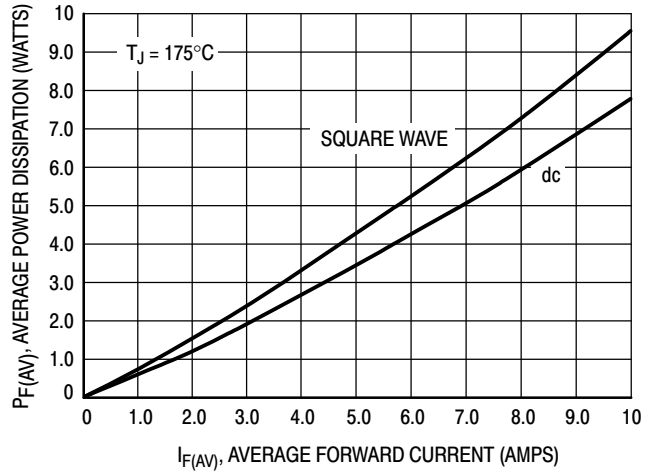


Figure 5. Power Dissipation

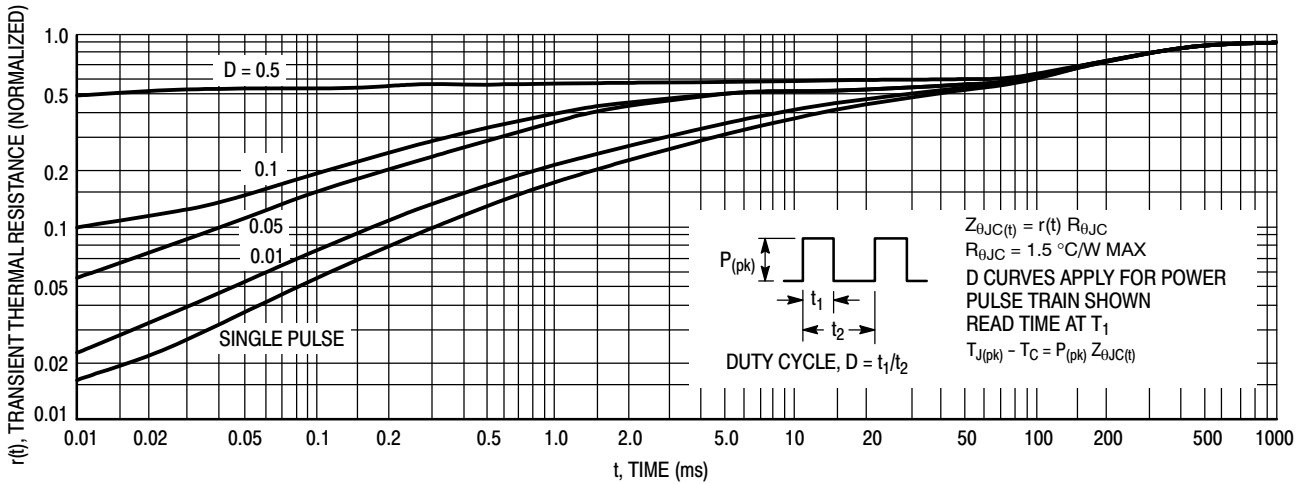


Figure 6. Thermal Response

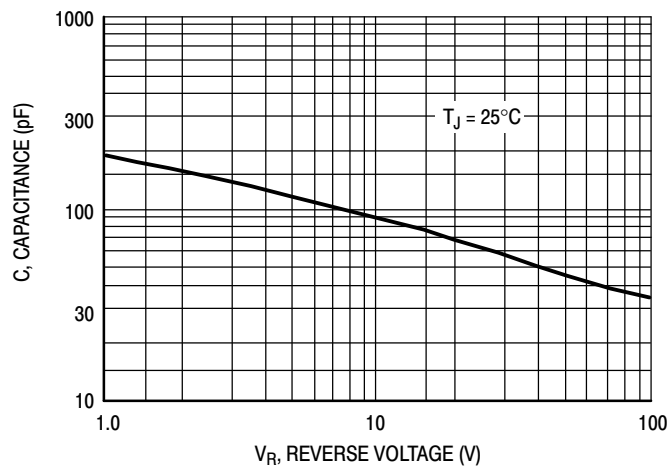
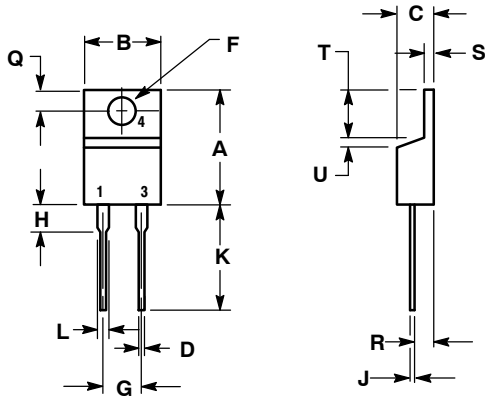


Figure 7. Typical Capacitance

BYW29-200


PACKAGE DIMENSIONS

TO-220
CASE 221B-04
ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.595	0.620	15.11	15.75
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
H	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

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